TRENCH
Gen5 TMOS

DIM1000H1HS17-PA500

Half Bridge IGBT Module

Replaces DS6249-4

DS6249-5 July 2021 (LN41081)

FEATURES

- Trench Gate IGBT
- Cu Base with Al_2O_3 Substrates
- 10µs Short Circuit Withstand

APPLICATIONS

- Motor Drives
- High Power Converters
- Renewable Energy Power Conversion
- High Reliability Inverters

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM1000H1HS17-PA500 is a Half Bridge 1700V, trench gate, insulated gate bipolar transistor (IGBT) module with enhanced field stop and implantation technology. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM1000H1HS17-PA500

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}		**1700V**
$V_{CE(sat)}$ *	**(typ)**	**1.85V**
I_C	**(max)**	**1000A**
$I_{C(PK)}$	**(max)**	**2000A**

* Measured at the auxiliary terminals

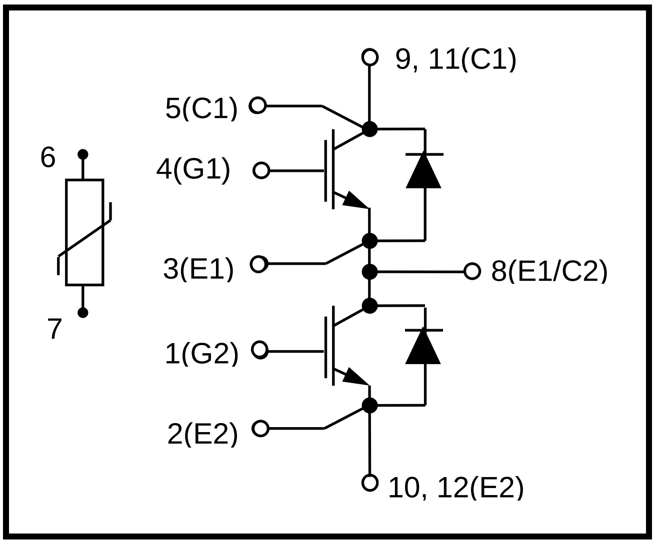
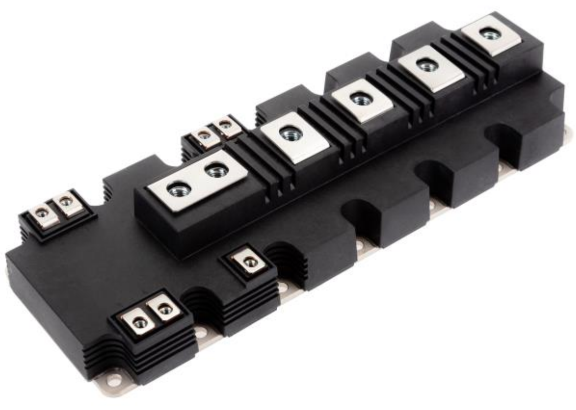


Fig. 1 Circuit configuration



Outline type code: H1

(See Fig. 15 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	V_{GE} = 0V, T_C = 25°C	1700	V
V_{GES}	Gate-emitter voltage	T_C = 25°C	±20	V
I_C	Continuous collector current	T_C = 104°C	1000	A
$I_{C(PK)}$	Peak collector current	t_P = 1ms T_C = 135°C	2000	A
P_{max}	Max. transistor power dissipation	T_C = 25°C, T_{vj} = 150°C	6.25	kW
I^2t	Diode I^2t value	V_R = 0, t_p = 10ms, T_{vj} = 150°C	145	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	4000	V

THERMAL AND MECHANICAL RATINGS

Internal insulation material: Al_2O_3

Baseplate material: Cu

Creepage distance: 33mm

Clearance: 19mm

CTI (Comparative Tracking Index): >400

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor	Continuous dissipation - junction to case	-	-	20	°C/kW
$R_{th(j-c)}$	Thermal resistance – diode	Continuous dissipation - junction to case	-	-	36	°C/kW
$R_{th(c-h)}$ IGBT	Thermal resistance – case to heatsink (IGBT)	Mounting torque 5Nm (with mounting grease: 1W/mK)	-	-	12	°C/kW
$R_{th(c-h)}$ Diode	Thermal resistance – case to heatsink (Diode)	Mounting torque 5Nm (with mounting grease: 1W/mK)	-	-	12	°C/kW
T_j	Junction temperature	Transistor	-40	-	150	°C
		Diode	-40	-	150	°C
T_{stg}	Storage temperature range	-	-40	-	150	°C
	Screw torque	Mounting – M5	3	-	6	Nm
		Electrical connections – M8	8	-	10	Nm

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector cut-off current	V_{GE} = 0V, V_{CE} = V_{CES}			1	mA
		V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 125°C			20	mA
		V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 150°C			30	mA
I_{GES}	Gate leakage current	V_{GE} = ± 20V, V_{CE} = 0V			0.5	μA
$V_{GE(TH)}$	Gate threshold voltage	I_C = 30mA, V_{GE} = V_{CE}	5.7	6.3	6.9	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15V, I_C = 1000A		1.85	2.25	V
		V_{GE} = 15V, I_C = 1000A, T_j = 125°C		2.20	2.60	V
		V_{GE} = 15V, I_C = 1000A, T_j = 150°C		2.30	2.70	V
I_F	Diode forward current	DC		1000		A
I_{FM}	Diode maximum forward current	t_p = 1ms		2000		A
V_F	Diode forward voltage	I_F = 1000A		1.8	2.2	V
		I_F = 1000A, T_j = 125°C		1.9	2.3	V
		I_F = 1000A, T_j = 150°C		1.9	2.3	V
C_{ies}	Input capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 100kHz		147		nF
Q_g	Gate charge	±15V		11.4		μC
C_{res}	Reverse transfer capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 100kHz		1.5		nF
L_M	Module inductance			10		nH
R_{INT}	Internal transistor resistance			0.2		mΩ
SC_{Data}	Short circuit current, I_{SC}	T_j = 150°C, V_{CC} = 1000V t_p ≤ 10μs, V_{GE} ≤ 15V $V_{CE\,(max)}$ = V_{CES} – L^* x dI/dt IEC 60747-9		4400		A

Note:
* L is the circuit inductance + L_M

NTC-Thermistor Data

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
R_{25}	Rated resistance	T_C = 25°C		5		kΩ
Δ*R*/R	Deviation of R100	T_C = 100°C, R_{100} = 493Ω	-5		5	%
P_{25}	Power dissipation	T_C = 25°C			20	mW
$B_{25/50}$	B-value	$R_2 = R_{25}\exp[B_{25/50}(1/T2 - 1/(298.15K))]$		3375		K
$B_{25/80}$		$R_2 = R_{25}\exp[B_{25/80}(1/T2 - 1/(298.15K))]$		3411		K
$B_{25/100}$		$R_2 = R_{25}\exp[B_{25/100}(1/T2 - 1/(298.15K))]$		3433		K

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions		Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	I_C = 1000A V_{CE} = 900V V_{GE} = ±15V $R_{G(OFF)}$ = 1.8Ω $R_{G(ON)}$ = 1.2Ω L_S ~ 20nH	*dv/dt* = 3000V/µs		1320		ns
t_f	Fall time				340		ns
E_{OFF}	Turn-off energy loss				280		mJ
$t_{d(on)}$	Turn-on delay time		*di/dt* = 7200A/µs		500		ns
t_r	Rise time				145		ns
E_{ON}	Turn-on energy loss				340		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 1000A V_{CE} = 900V *di/dt* = 7200A/µs			285		µC
I_{rr}	Diode reverse recovery current				520		A
E_{rec}	Diode reverse recovery energy				110		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions		Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	I_C = 1000A V_{CE} = 900V V_{GE} = ±15V $R_{G(OFF)}$ = 1.8Ω $R_{G(ON)}$ = 1.2Ω L_S ~ 20nH	*dv/dt* = 3000V/µs		1410		ns
t_f	Fall time				440		ns
E_{OFF}	Turn-off energy loss				350		mJ
$t_{d(on)}$	Turn-on delay time		*di/dt* = 7200A/µs		470		ns
t_r	Rise time				145		ns
E_{ON}	Turn-on energy loss				370		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 1000A V_{CE} = 900V *di/dt* = 7200A/µs			315		µC
I_{rr}	Diode reverse recovery current				620		A
E_{rec}	Diode reverse recovery energy				210		mJ

T_{case} = 150°C unless stated otherwise

Symbol	Parameter	Test Conditions		Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	I_C = 1000A V_{CE} = 900V V_{GE} = ±15V $R_{G(OFF)}$ = 1.8Ω $R_{G(ON)}$ = 1.2Ω L_S ~ 20nH	*dv/dt* = 3000V/µs		1440		ns
t_f	Fall time				570		ns
E_{OFF}	Turn-off energy loss				360		mJ
$t_{d(on)}$	Turn-on delay time		*di/dt* = 7200A/µs		460		ns
t_r	Rise time				140		ns
E_{ON}	Turn-on energy loss				385		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 1000A V_{CE} = 900V *di/dt* = 7200A/µs			340		µC
I_{rr}	Diode reverse recovery current				655		A
E_{rec}	Diode reverse recovery energy				235		mJ

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

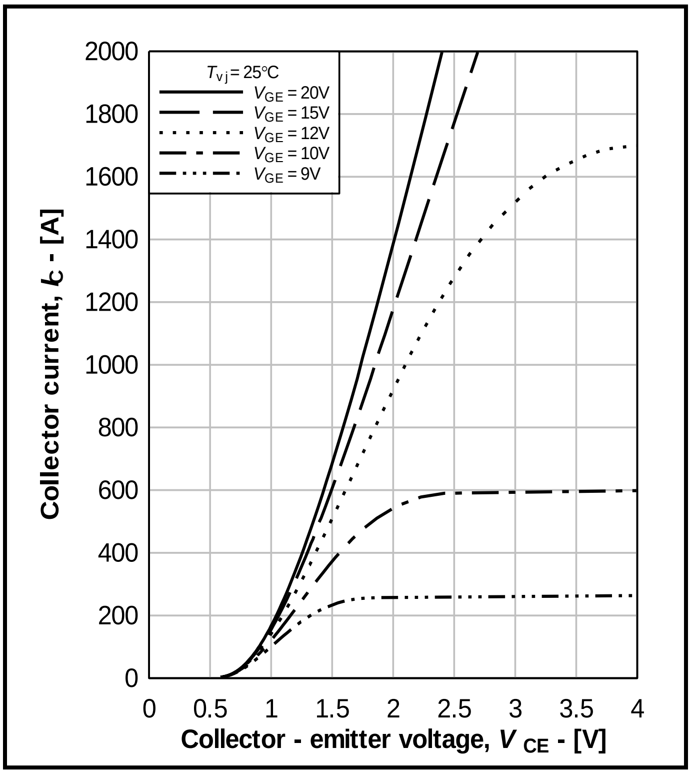


Fig. 3 Typical IGBT output characteristics, $I_C = f(V_{CE})$

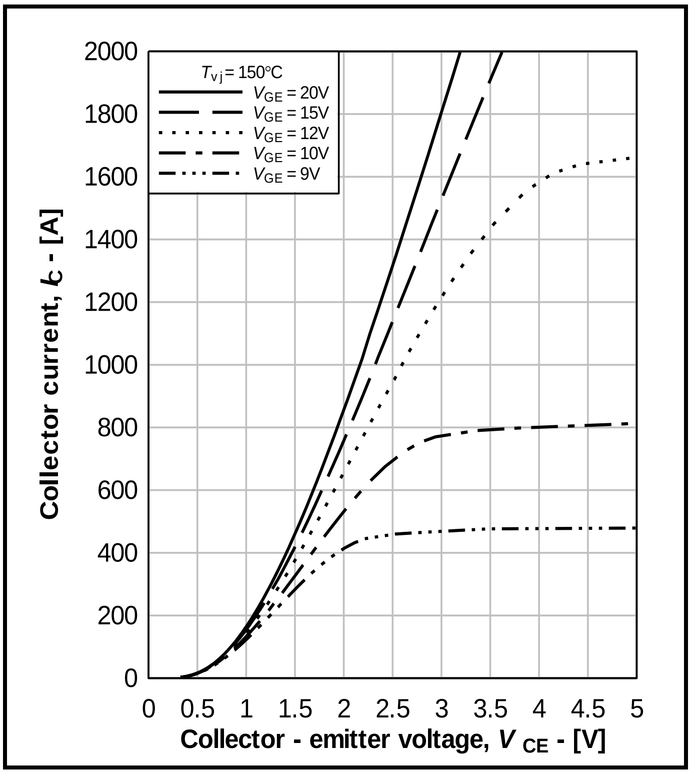


Fig. 4 Typical IGBT output characteristics, $I_C = f(V_{CE})$

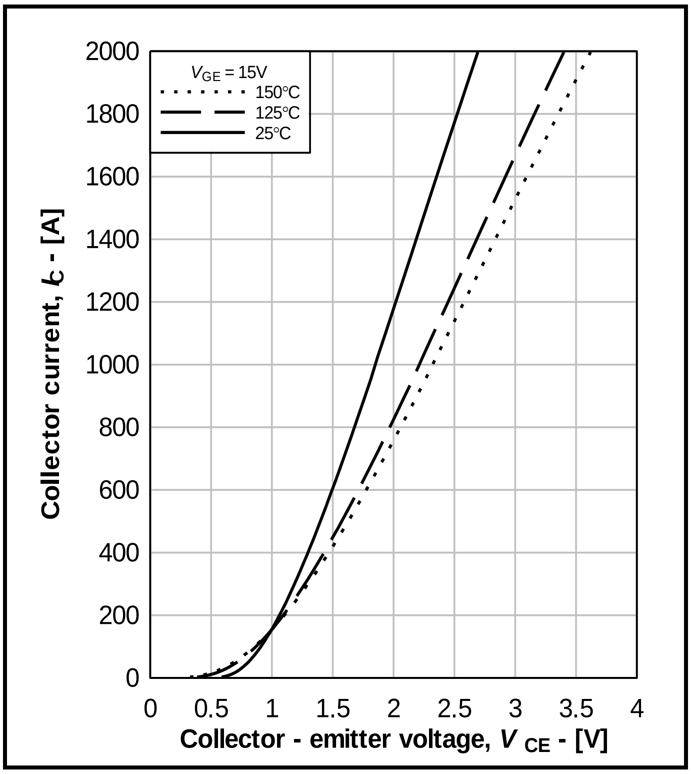


Fig. 5 Typical IGBT output characteristics, $I_C = f(V_{CE})$

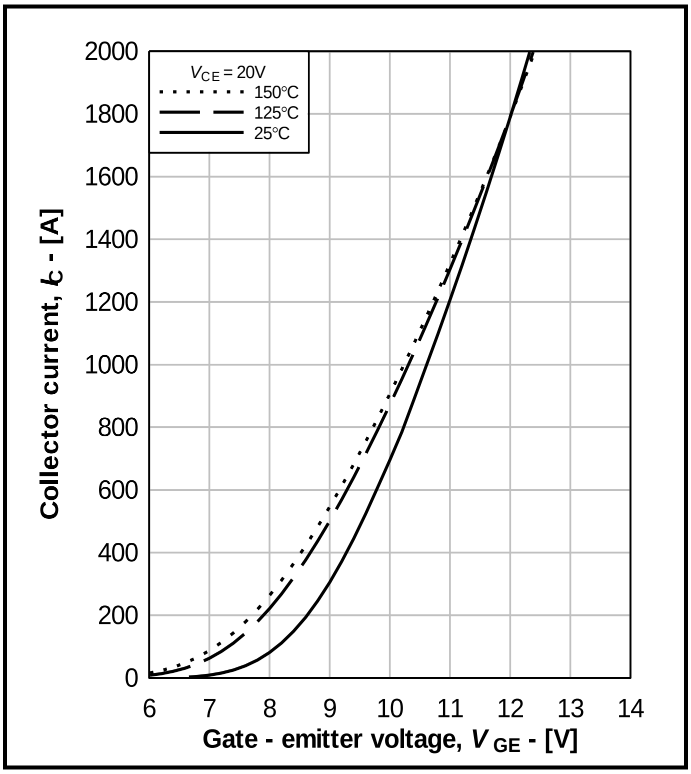


Fig. 6 Typical IGBT transfer characteristics, $I_C = f(V_{GE})$

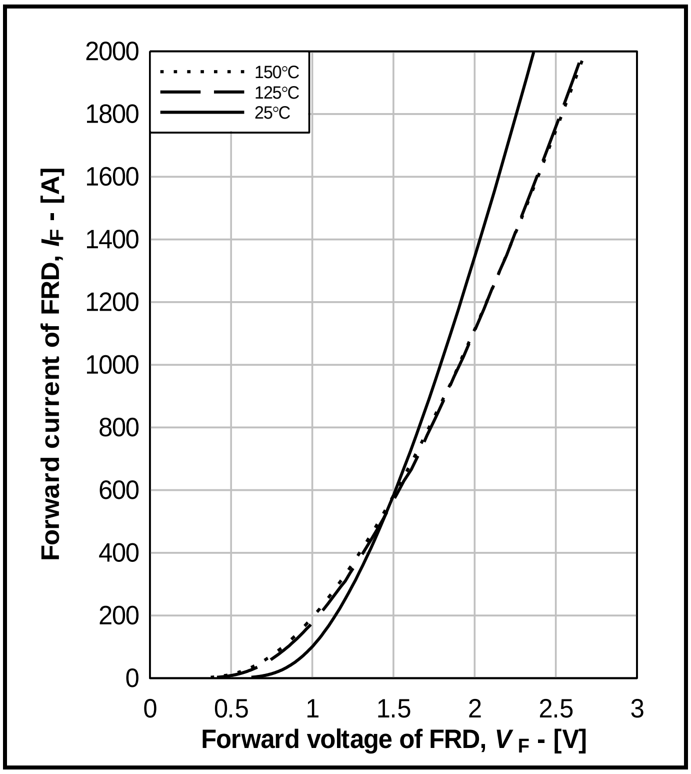


Fig. 7 Diode typical forward characteristics, $I_F = f(V_F)$

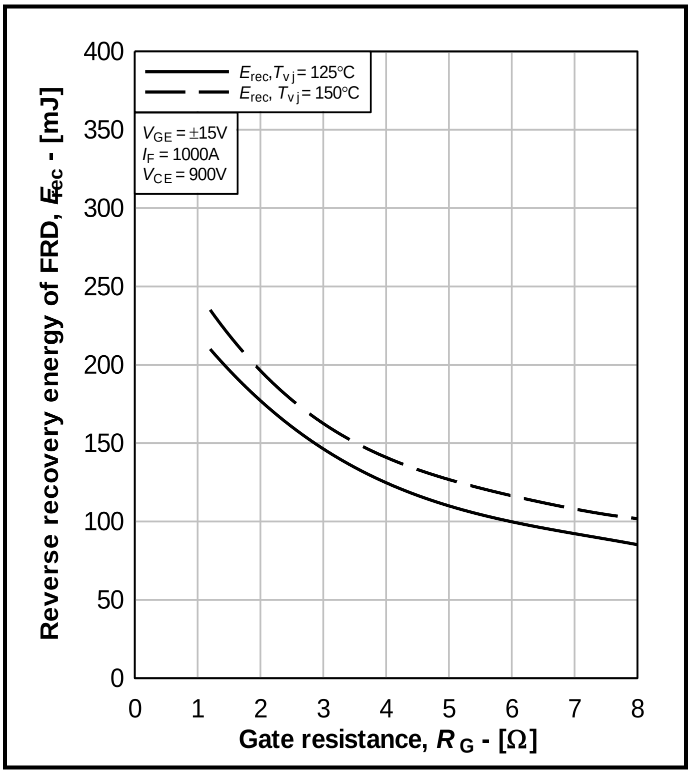


Fig. 8 Typical FRD E_{rec}, $E_{rec} = f(R_G)$

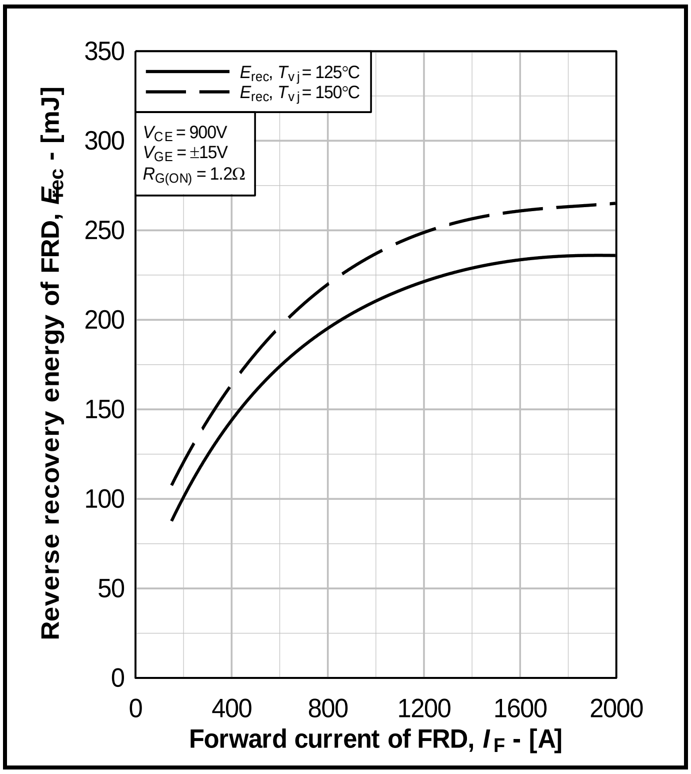


Fig. 9 Typical FRD E_{rec}, $E_{rec} = f(I_F)$

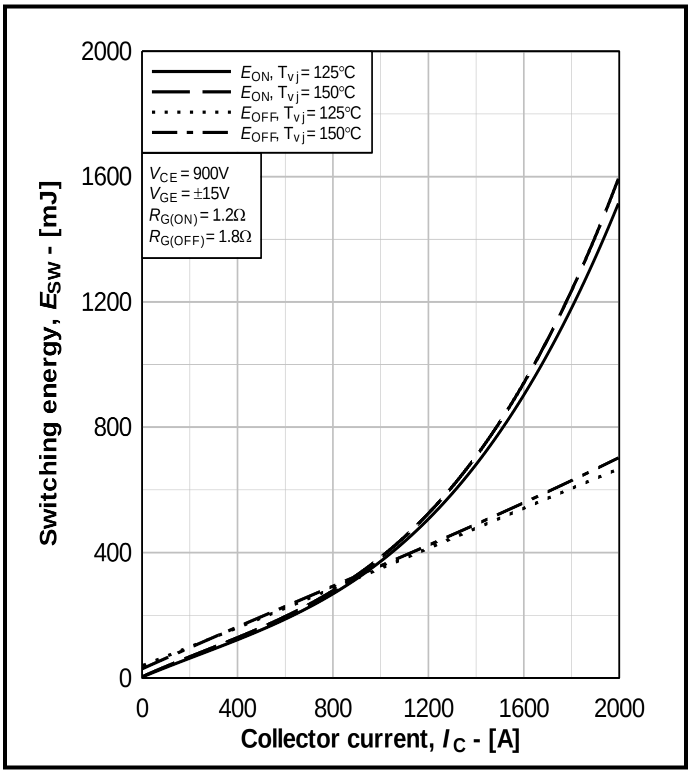


Fig. 10 Typical IGBT switching energy, $E_{ON} = f(I_C)$, $E_{OFF} = f(I_C)$

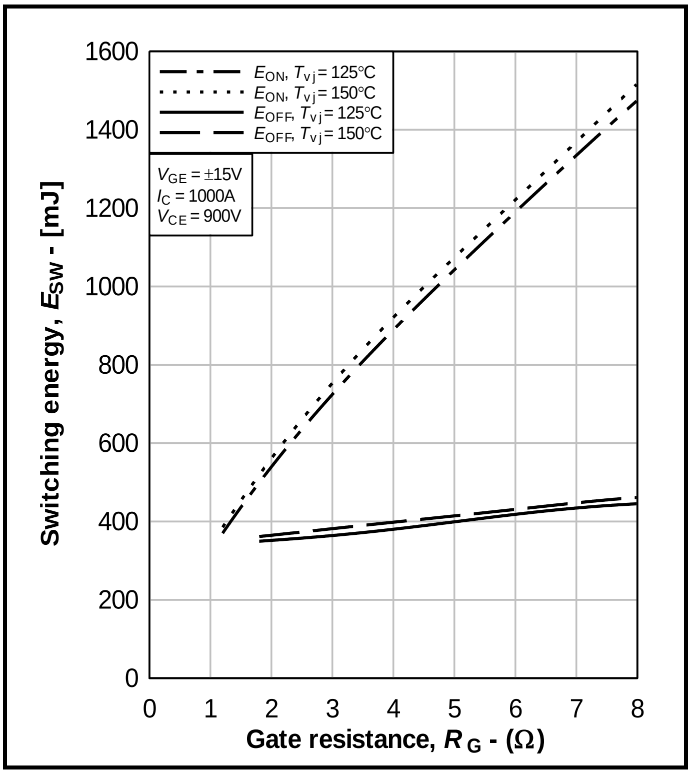


Fig. 11 Typical IGBT switching energy $E_{ON} = f(R_G)$, $E_{OFF} = f(R_G)$

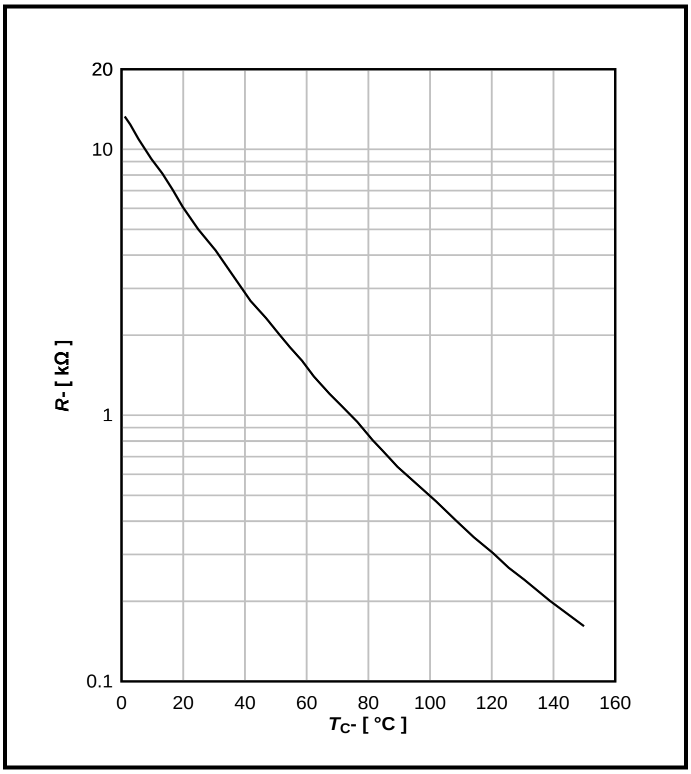


Fig. 12 Typical NTC thermistor characteristic, $R = f(T_C)$

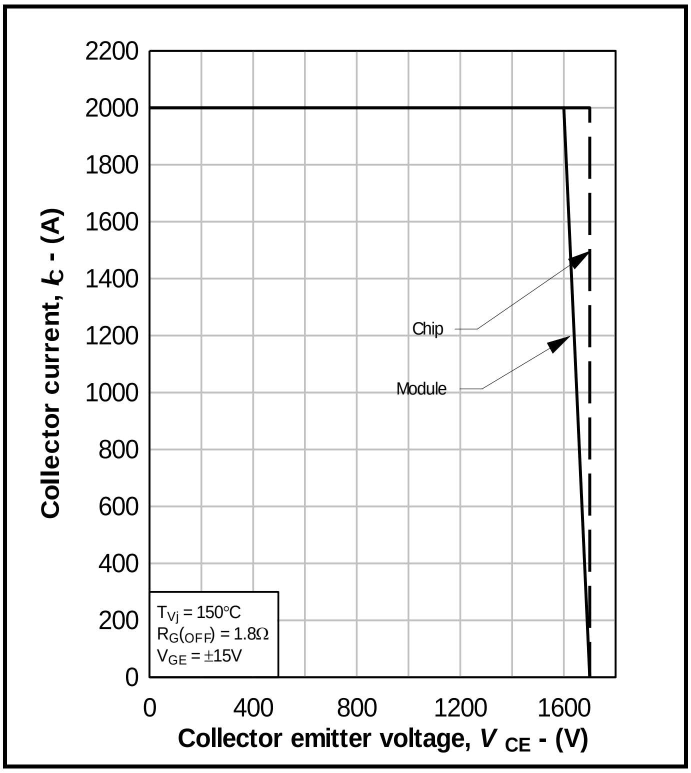


Fig. 13 Reverse bias safe operating area of IGBT, $I_C = f(V_{CE})$

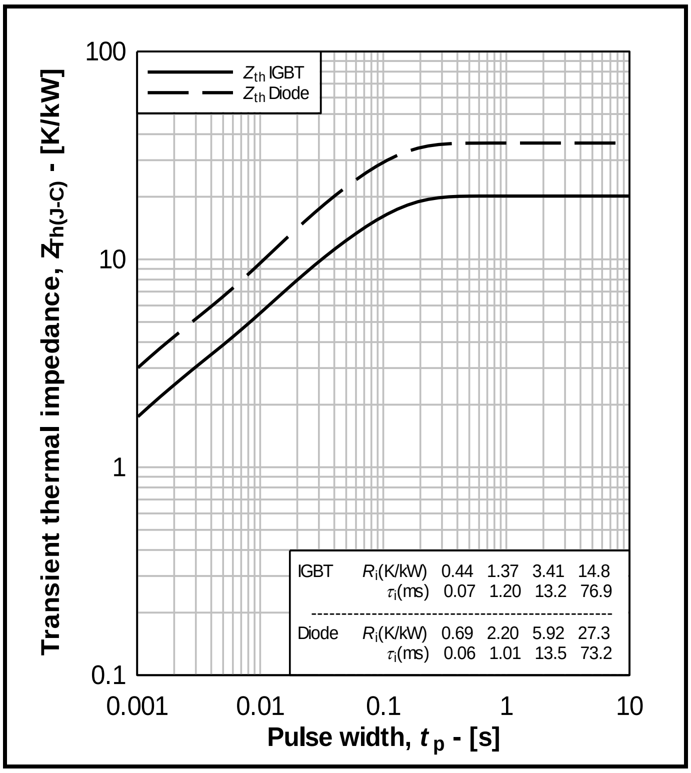
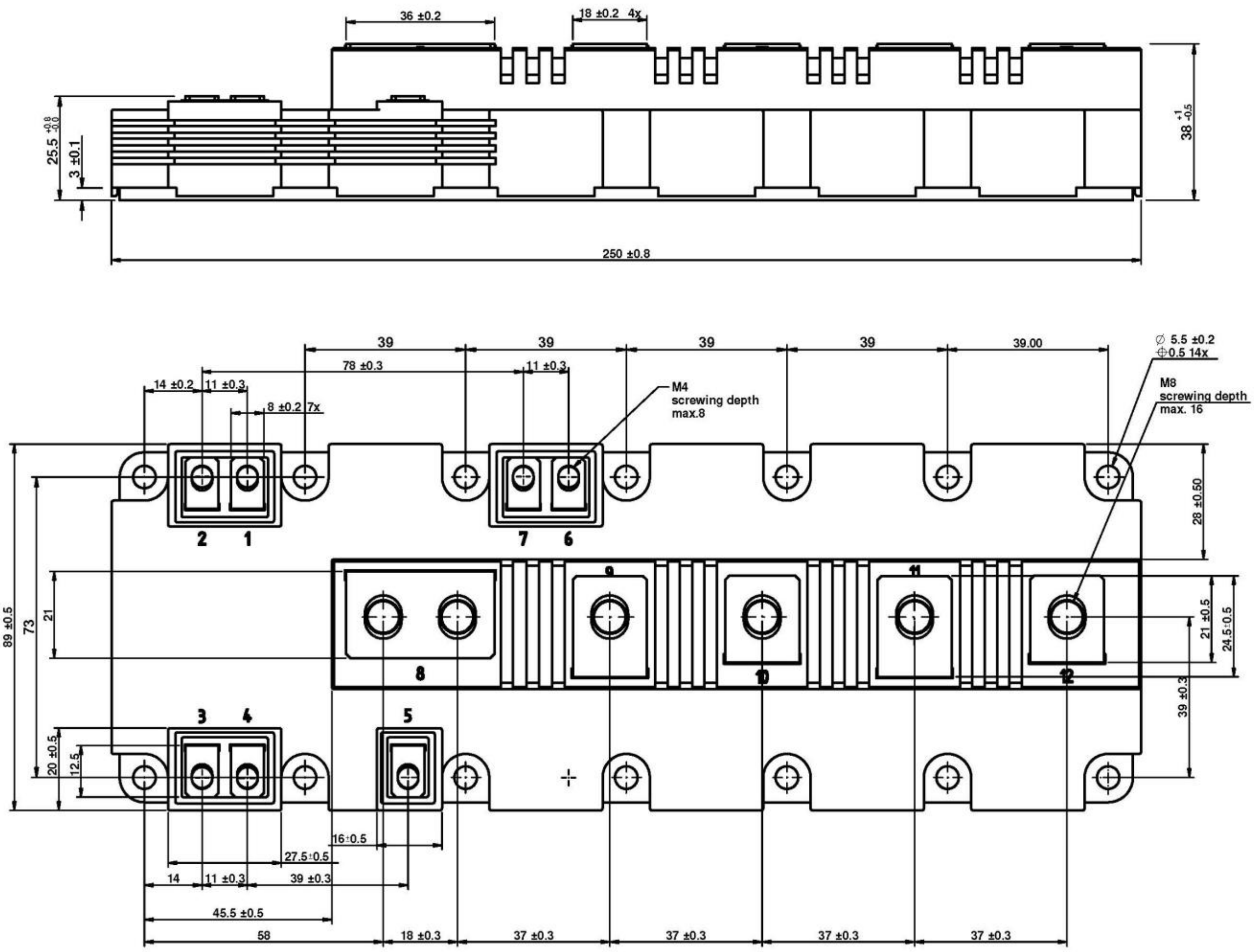


Fig. 14 Transient thermal impedance, $Z_{th(J-C)} = f(t)$

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal Weight: 1200g

Module Outline Type Code: H1

Fig. 15 Module outline drawing

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

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The products must not be touched when operating because there is a danger of electrocution or severe burning. Always use protective safety equipment such as appropriate shields for the product and wear safety glasses. Even when disconnected any electric charge remaining in the product must be discharged and allowed to cool before safe handling using protective gloves.

Extended exposure to conditions outside the product ratings may affect reliability leading to premature product failure. Use outside the product ratings is likely to cause permanent damage to the product. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture, a large current to flow or high voltage arcing, resulting in fire or explosion. Appropriate application design and safety precautions should always be followed to protect persons and property.

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Preliminary Information: The product design is complete and final characterisation for volume production is in progress. The datasheet represents the product as it is now understood but details may change.

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HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LTD
Doddington Road, Lincoln, Lincolnshire, LN6 3LF,
United Kingdom
Tel: +44(0)1522 500500
Web: http://www.dynexsemi.com

CUSTOMER SERVICE

DYNEX SEMICONDUCTOR LTD
Doddington Road, Lincoln, Lincolnshire, LN6 3LF,
United Kingdom
Tel: +44(0)1522 502753 / 502901
Email: powersolutions@dynexsemi.com